



STS11NF3LL

N-CHANNEL 30V - 0.008Ω - 11A SO-8 LOW GATE CHARGE STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STS11NF3LL	30 V	< 0.011 Ω	11 A

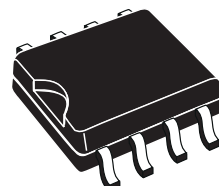
- TYPICAL R_{DS(on)} = 0.011Ω @ 4.5V
- OPTIMAL R_{DS(on)} Q_g TRADE-OFF @4.5V
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED

DESCRIPTION

This application specific Power MOSFET is the third generation of STMicroelectronics unique "Single Feature Size" strip-based process. The resulting transistor shows the best trade-off between on-resistance and gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

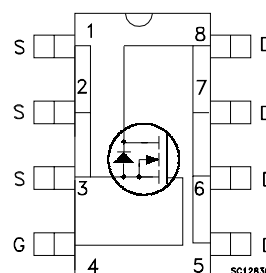
APPLICATIONS

- SPECIFICALLY DESIGNED AND OPTIMISED FOR HIGH EFFICIENCY CPU CORE DC/DC CONVERTERS FOR MOBILE PCs



SO-8

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C (*) Drain Current (continuous) at T _C = 100°C	11 7	A A
I _{DM} (●)	Drain Current (pulsed)	44	A
P _{TOT}	Total Dissipation at T _C = 25°C	2.5	W

(●) Pulse width limited by safe operating area

(*)Value limited by wires bonding

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THERMAL DATA

Rthj-amb	Thermal Resistance Junction-ambient Max (#)	50	°C/W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	–65 to 150	°C

(#) When Mounted on a 1inch² pad

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 5.5 A V _{GS} = 4.5 V, I _D = 5.5 A		0.008 0.011	0.011 0.013	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 5.5 A		15		S
C _{iss}	Input Capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0		1700		pF
C _{oss}	Output Capacitance			505		pF
C _{rss}	Reverse Transfer Capacitance			115		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 5.5\text{ A}$		20		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, see Fig. 3)		70		ns
Q_g	Total Gate Charge	$V_{DD} = 15\text{ V}$, $I_D = 11\text{ A}$,		21	28	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 4.5\text{ V}$		9.5		nC
Q_{gd}	Gate-Drain Charge			10		nC

SWITCHING OFF

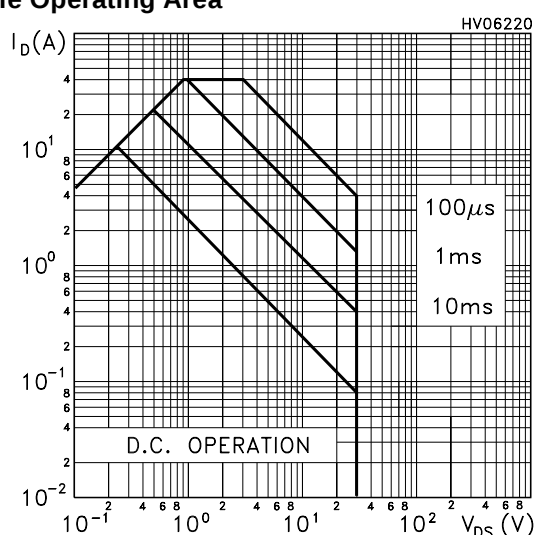
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 5.5\text{ A}$,		40		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load see, Fig. 3)		20		ns

SOURCE DRAIN DIODE

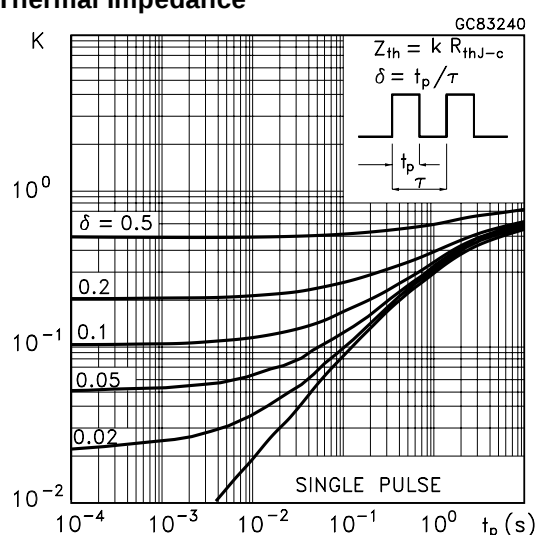
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				11	A
$I_{SDM} (1)$	Source-drain Current (pulsed)				44	A
$V_{SD} (2)$	Forward On Voltage	$I_{SD} = 11\text{ A}$, $V_{GS} = 0$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		45		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$		52		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		2.3		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

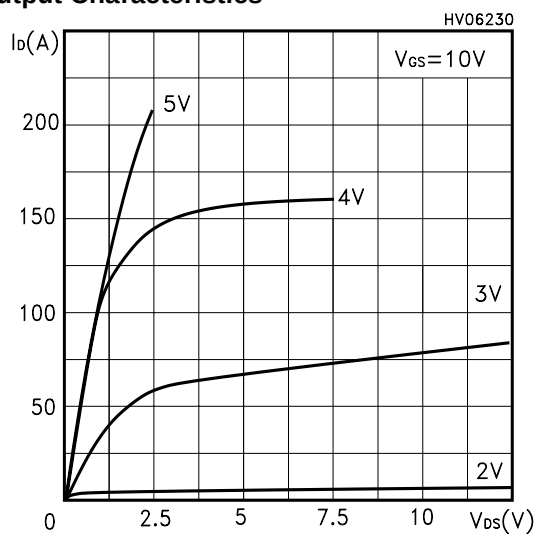
Safe Operating Area



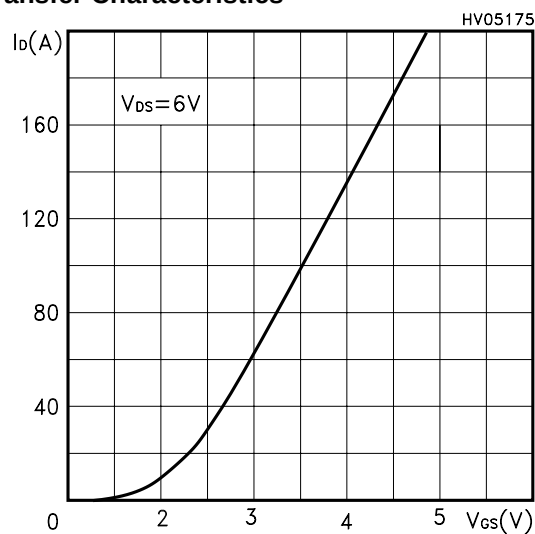
Thermal Impedance



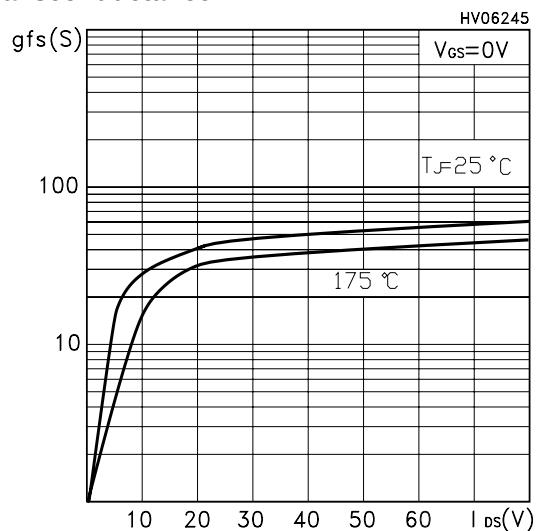
Output Characteristics



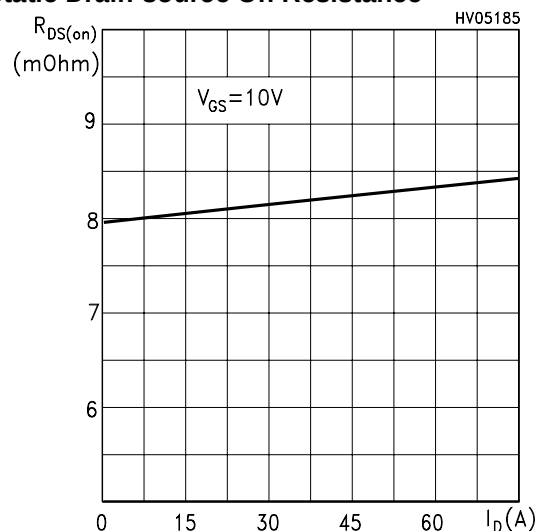
Transfer Characteristics



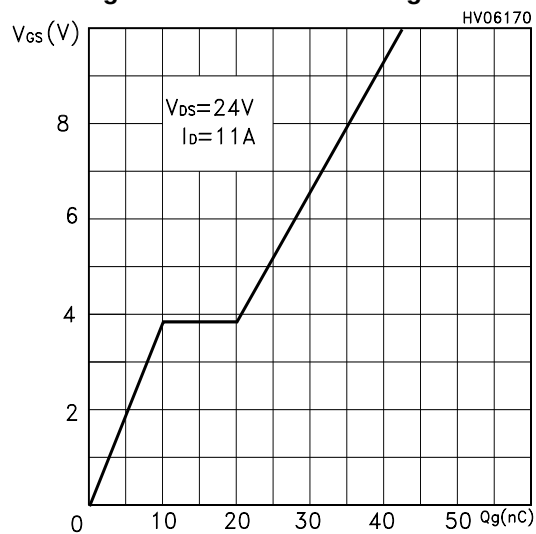
Transconductance



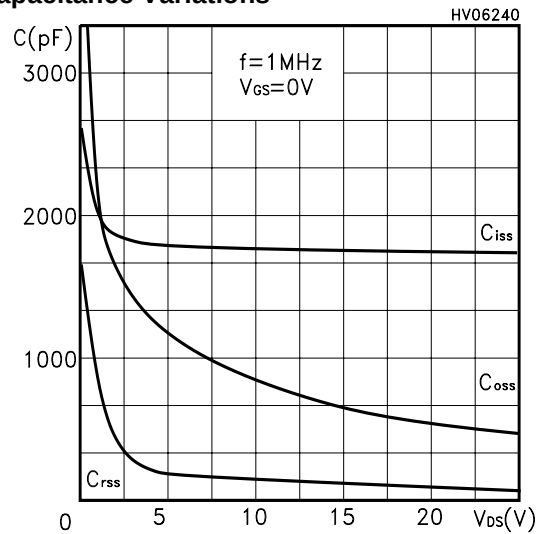
Static Drain-source On Resistance



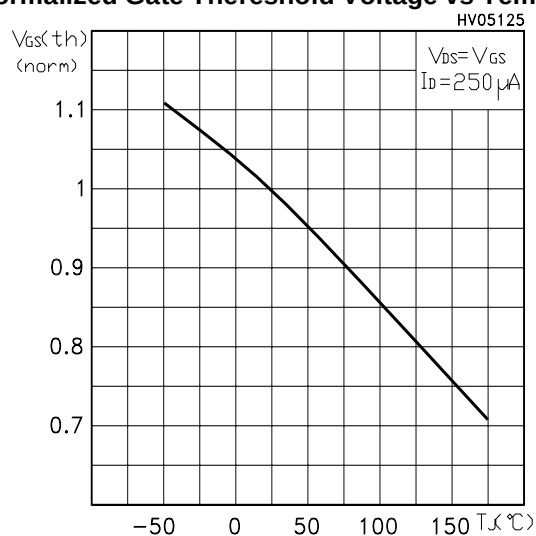
Gate Charge vs Gate-source Voltage



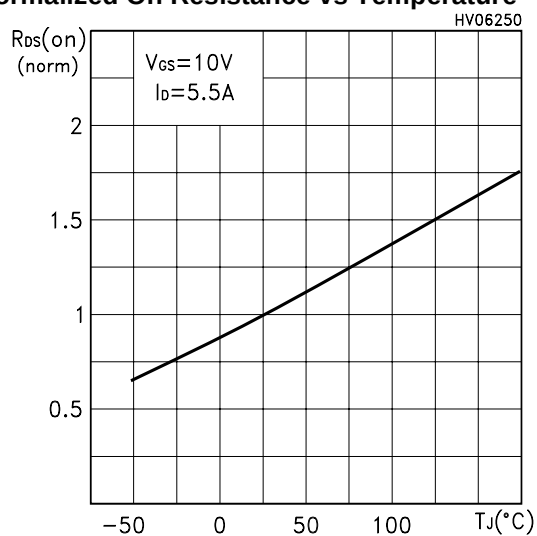
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

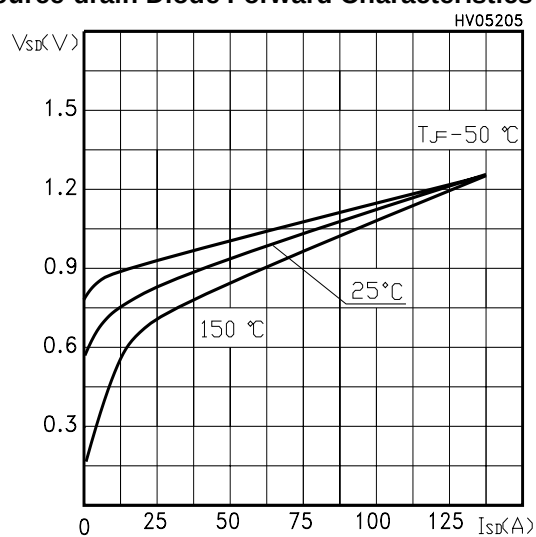


Fig. 1: Unclamped Inductive Load Test Circuit

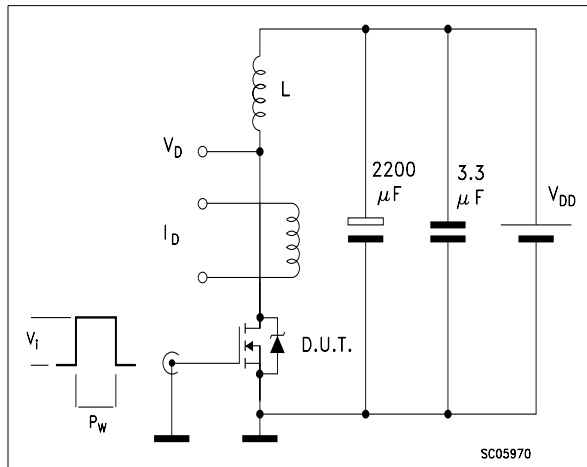


Fig. 2: Unclamped Inductive Waveform

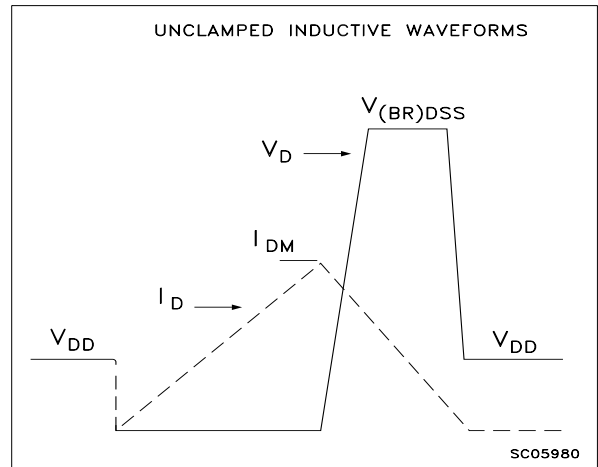


Fig. 3: Switching Times Test Circuit For Resistive Load

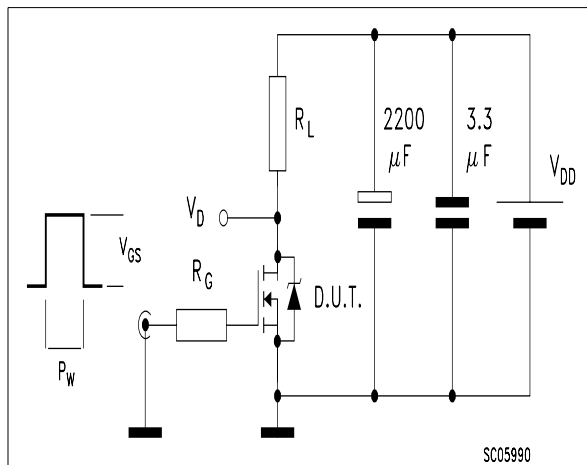


Fig. 4: Gate Charge test Circuit

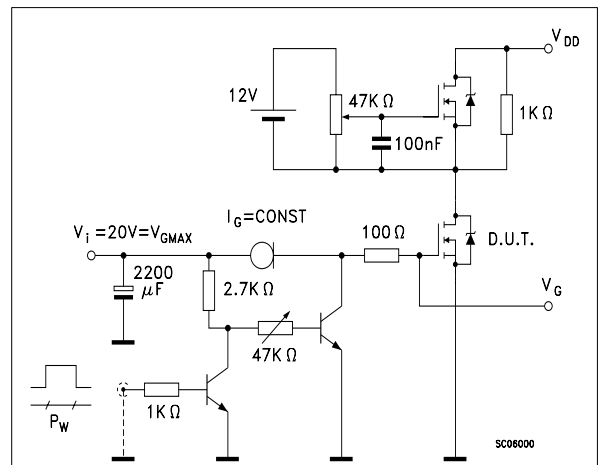
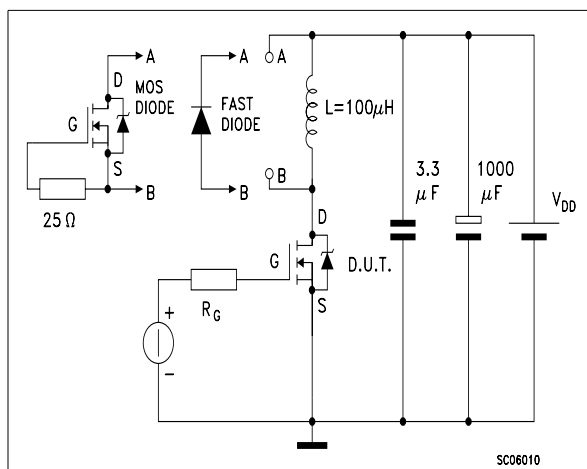
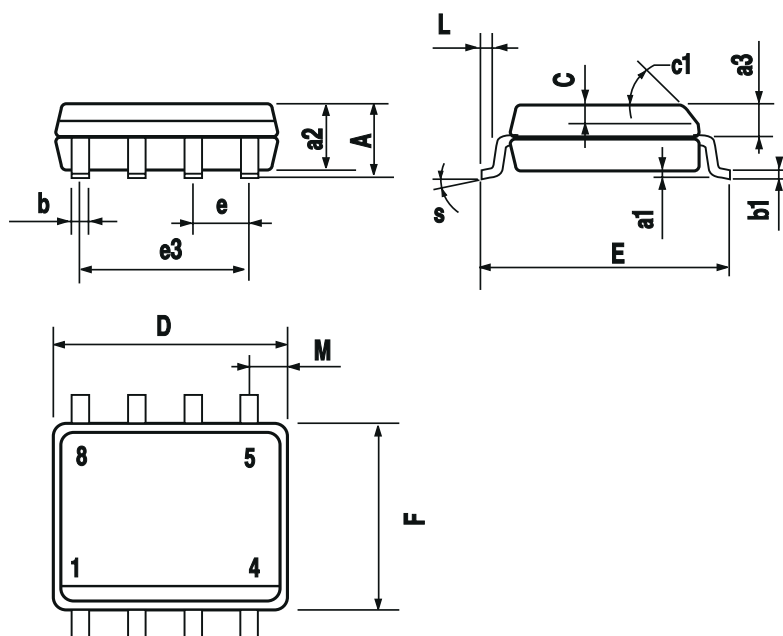


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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